

IN THE CLAIMS:

Please amend claims 1, 4, 19, 21, and 23 as follows:

1. (Currently Amended) A method of using SACVD deposition to deposit at least one layer of dielectric material inside a deposition reactor during the fabrication of at least one semiconductor integrated circuit, said method comprising the steps of:

providing a reaction chamber for carrying out SACVD deposition;

supplying a stream of a first reaction gas containing oxygen plasma into a first gas feed conduit connected to the reaction chamber;

applying microwaves inside the first gas feed conduit in order to produce sufficient oxygen radicals from the oxygen plasma, the oxygen radicals being necessary to initiate SACVD deposition;

supplying a stream of a second reaction gas into the reaction chamber through a second gas feed conduit, the second reaction gas being suitable to initiate SACVD deposition when reacting with oxygen radicals; and

supplying the first reaction gas, in which sufficient oxygen radicals have been produced from oxygen plasma, from the first gas feed conduit into the reaction chamber to perform an SACVD deposition within the reaction chamber through reaction of oxygen radicals with the second reaction gas.

2. (Original) The method as defined in claim 1,

wherein in the step of supplying the stream of the first reaction gas, the first reaction gas is oxygen, and

in the step of applying microwaves, an oxygen plasma containing oxygen radicals is produced.

3. (Original) The method as defined in claim 1, wherein the microwave activation pressure is 1.5 Torr.

4. (Currently Amended) The method as defined in claim 1, wherein in the step of supplying the first reaction gas ~~in which sufficient oxygen radicals have been produced from oxygen plasma from the first gas feed conduit~~ into the reaction chamber, a remote plasma of the first reaction gas is forced into the reaction chamber.

5. (Original) The method as defined in claim 1, wherein the reaction pressure is within the range of 1 to 700 Torr.

6-16. (Canceled)

17. (Original) The method as defined in claim 1, wherein ozone is not supplied as a process gas in performing the SACVD deposition within the reaction chamber.

18. (Original) The method as defined in claim 2, wherein ozone is not supplied as a process gas in performing the SACVD deposition within the reaction chamber.

19. (Currently Amended) A method of using SACVD deposition to deposit at least one layer of dielectric material inside a deposition reactor during the fabrication of at least one semiconductor integrated circuit, said method comprising the steps of:

supplying an oxygen plasma into a gas feed conduit connected to a reaction chamber;  
applying microwaves to the oxygen plasma in the gas feed conduit in order to produce sufficient free oxygen radicals from the oxygen plasma to initiate SACVD deposition; and  
supplying the free oxygen radicals, ~~which that~~ have been produced in the gas feed conduit, from the gas feed conduit into the reaction chamber of the reactor to perform SACVD deposition within the reaction chamber through reaction of the oxygen radicals.

20. (Original) The method as defined in claim 19, wherein the microwave activation pressure is 1.5 Torr.

21. (Currently Amended) The method as defined in claim 19, wherein in the step of supplying the free oxygen radicals ~~into the reaction chamber~~, the free oxygen radicals are forced into the reaction chamber.

22. (Original) The method as defined in claim 19, wherein ozone is not supplied as a process gas in performing the SACVD deposition within the reaction chamber.

23. (Currently Amended) The method as defined in claim 19, wherein the step of applying microwaves includes the sub-steps of:

receiving, from a first portion of the gas feed conduit, the oxygen plasma that is supplied at a magnetron;

operating the magnetron to produce the microwaves that are applied to the oxygen plasma; and

discharging a stream of the oxygen plasma from the magnetron to a second portion of the gas feed conduit that is connected to the reaction chamber.

24. (Original) A method of using SACVD deposition to deposit at least one layer of dielectric material inside a deposition reactor during the fabrication of at least one semiconductor integrated circuit, said method comprising the steps of:

providing a reaction chamber for carrying out SACVD deposition;

supplying a stream of oxygen to a magnetron;

operating the magnetron to produce microwaves so as to generate within the magnetron an oxygen plasma containing sufficient free oxygen radicals to initiate SACVD deposition;

discharging a stream of the oxygen plasma from the magnetron; and

supplying the stream of the oxygen plasma from the magnetron into the reaction chamber to perform SACVD deposition within the reaction chamber through reaction of the oxygen radicals.

25. (Original) The method as defined in claim 24, wherein the microwave activation pressure is 1.5 Torr.

26. (Original) The method as defined in claim 24, wherein in the step of supplying the stream of the oxygen plasma into the reaction chamber, the stream of the oxygen plasma is forced into the reaction chamber.

27. (Original) The method as defined in claim 24, wherein ozone is not supplied as a process gas in performing the SACVD deposition within the reaction chamber.